

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

SS8550-MS

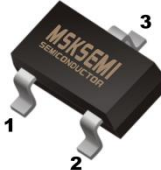

Product specification

TRANSISTOR (PNP)

FEATURES

- High Collector Current
- Complementary to SS8050-MS

Reference News

| PACKAGE OUTLINE | MARKING |
|--|---|
|  <p>1. BASE 2. EMITTER 3. COLLECTOR</p> |  |
| SOT-23 | |

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

| Symbol | Parameter | Value | Unit |
|------------------|---|------------|------|
| V _{CB0} | Collector-Base Voltage | -40 | V |
| V _{CEO} | Collector-Emitter Voltage | -25 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| I _c | Collector Current | -1.5 | A |
| P _c | Collector Power Dissipation | 300 | mW |
| R _{θJA} | Thermal Resistance From Junction To Ambient | 417 | °C/W |
| T _j | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -55 ~ +150 | °C |

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

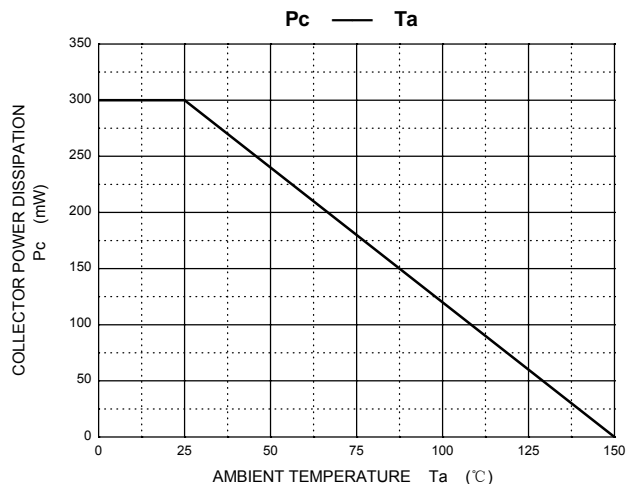
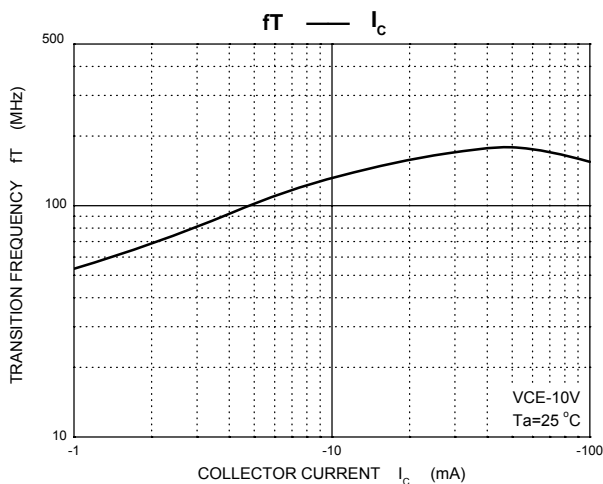
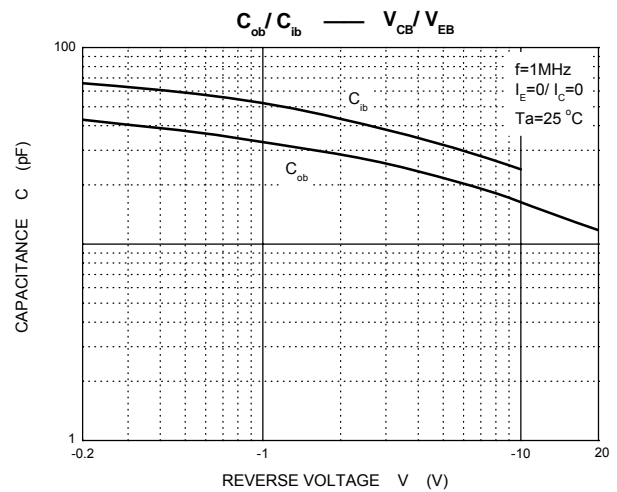
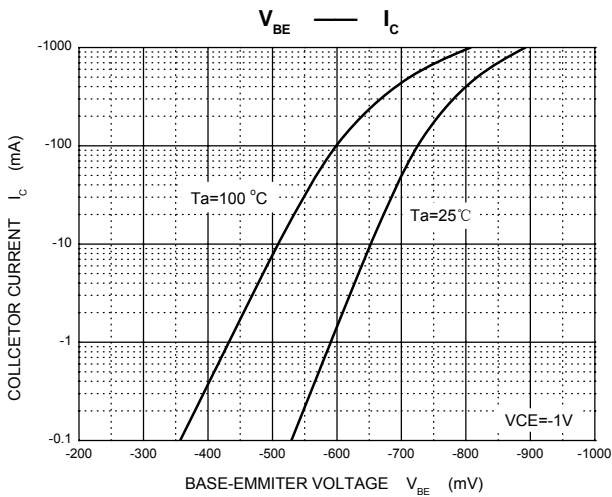
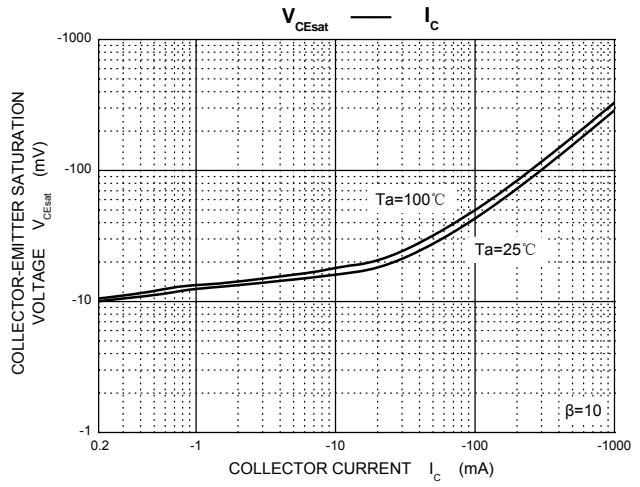
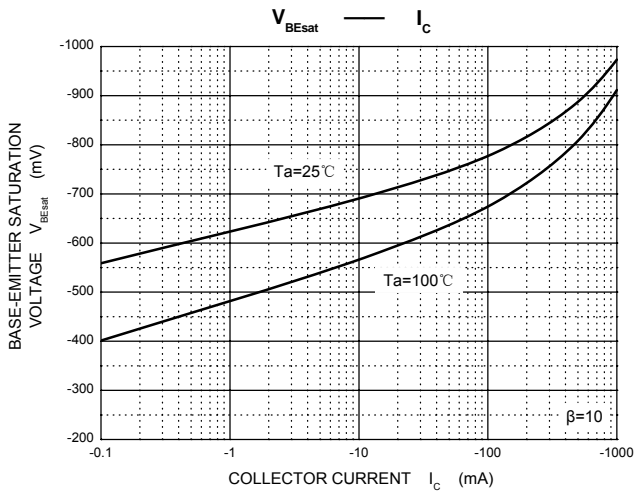
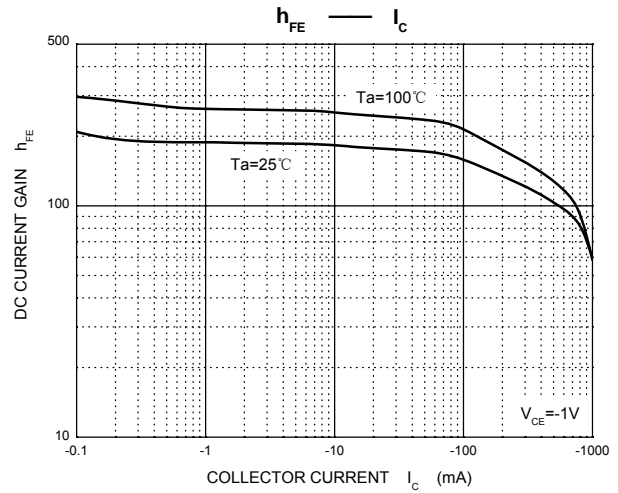
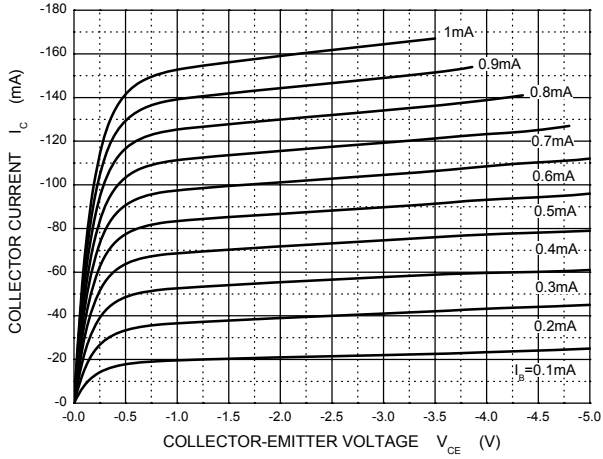
| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|----------------------|---|-----|-----|------|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _c =-100μA, I _E =0 | -40 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | I _c =-0.1mA, I _B =0 | -25 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =-100μA, I _c =0 | -5 | | | V |
| Collector cut-off current | I _{CBO} | V _{CB} =-40V, I _E =0 | | | -100 | nA |
| Collector cut-off current | I _{CEO} | V _{CE} =-20V, I _B =0 | | | -100 | nA |
| Emitter cut-off current | I _{EBO} | V _{EB} =-5V, I _c =0 | | | -100 | nA |
| DC current gain | h _{FE(1)} | V _{CE} =-1V, I _c =-100mA | 120 | | 400 | |
| | h _{FE(2)} | V _{CE} =-1V, I _c =-800mA | 40 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _c =-800mA, I _B =-80mA | | | -0.5 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | I _c =-800mA, I _B =-80mA | | | -1.2 | V |
| Base-emitter voltage | V _{BE} | V _{CE} =-1V, I _c =-10mA | | | -1 | V |
| Transition frequency | f _T | V _{CE} =-10V, I _c =-50mA, f=30MHz | 100 | | | MHz |
| Collector output capacitance | C _{ob} | V _{CB} =-10V, I _E =0, f=1MHz | | | 20 | pF |

CLASSIFICATION OF h_{FE(1)}

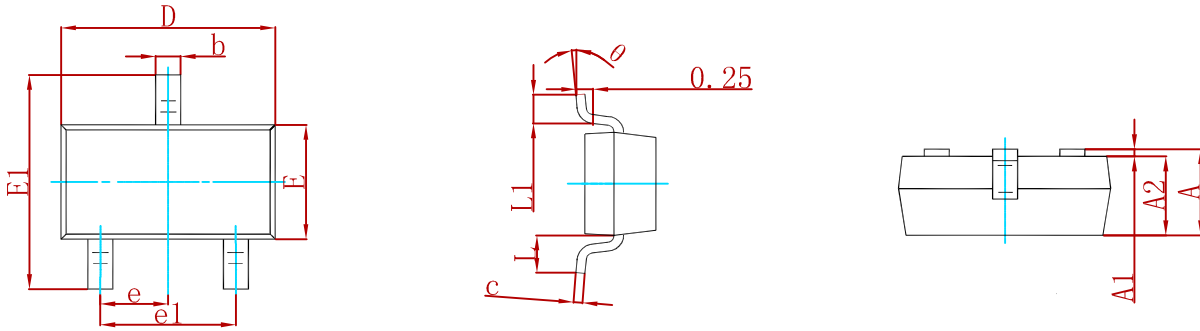
| RANK | L | H | J |
|-------|----------|----------|----------|
| RANGE | 120 -200 | 200 -350 | 300 -400 |

Typical Characteristics

Static Characteristic

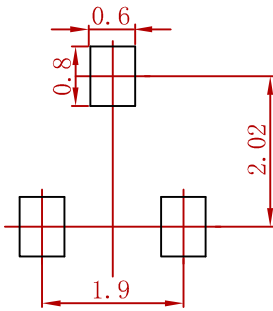


PACKAGE MECHANICAL DATA



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP | | 0.037 TYP | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF | | 0.022 REF | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| θ | 0° | 8° | 0° | 8° |

Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05mm.
 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

| P/N | PKG | QTY |
|-----------|--------|------|
| SS8550-MS | SOT-23 | 3000 |

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